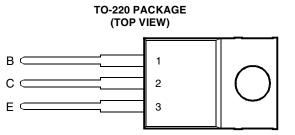
TIP29D, TIP29E, TIP29F NPN SILICON POWER TRANSISTORS

BOURNS®

- 30 W at 25°C Case Temperature
- 1 A Continuous Collector Current
- 3 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	TIP29D		160		
Collector-base voltage ($I_E = 0$)	TIP29E	V _{CBO}	180	V	
	TIP29F		200		
	TIP29D		120		
Collector-emitter voltage (I _B = 0)	TIP29E	V _{CEO}	140	v	
	TIP29F		160		
Emitter-base voltage			5	V	
Continuous collector current			1	A	
Peak collector current (see Note 1)			3	A	
Continuous base current	I _B	0.4	A		
Continuous device dissipation at (or below) 25°C case temperature (s	P _{tot}	30	W		
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W	
Unclamped inductive load energy (see Note 4)	½Ll _C ²	32	mJ		
Operating junction temperature range	Тj	-65 to +150	°C		
Storage temperature range	T _{stg}	-65 to +150	°C		
Lead temperature 3.2 mm from case for 10 seconds			250	°C	

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

2. Derate linearly to 150°C case temperature at the rate of 0.24 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = 0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = 20 V.



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electrical characteristics at 25°C case temperature

PARAMETER			TEST CONDITI	ST CONDITIONS			MAX	UNIT
V(DD)OFO	Collector-emitter breakdown voltage			TIP29D	120			
		I _C = 30 mA	$I_B = 0$	TIP29E	140			V
		(see Note 5)		TIP29F	160			
I _{CES}	Collector-emitter cut-off current	V _{CE} = 160 V	$V_{BE} = 0$	TIP29D			0.2	
		V _{CE} = 180 V	$V_{BE} = 0$	TIP29E			0.2	mA
		V _{CE} = 200 V	$V_{BE} = 0$	TIP29F			0.2	
I _{CEO}	Collector cut-off current	V _{CE} = 90 V	$I_B = 0$				0.3	mA
I _{EBO}	Emitter cut-off	V _{EB} = 5 V	$I_{\rm C} = 0$				1	mA
Ebo	current		Ũ					
h _{FE}	Forward current	$V_{CE} = 4 V$	$I_{\rm C} = 0.2 {\rm A}$	(see Notes 5 and 6)	40			
	transfer ratio	$V_{CE} = 4 V$	I _C = 1 A		15			
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = 125 mA	$I_{\rm C} = 1 {\rm A}$	(see Notes 5 and 6)			0.7	V
V_{BE}	Base-emitter voltage	V _{CE} = 4 V	I _C = 1 A	(see Notes 5 and 6)			1.3	V
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	I _C = 0.2 A	f = 1 kHz	20			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	I _C = 0.2 A	f = 1 MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu s$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
R_{\thetaJC}	Junction to case thermal resistance			4.17	°C/W
R_{\thetaJA}	Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

PAR	RAMETER	TEST CONDITIONS [†]			MIN	ТҮР	MAX	UNIT
t _{on} Tur	rn-on time	I _C = 1 A	$I_{B(on)} = 0.1 A$	$I_{B(off)} = -0.1 A$		0.5		μs
t _{off} Tur	rn-off time	$V_{BE(off)} = -4.3 V$	$R_L = 30 \Omega$	t_p = 20 µs, dc \leq 2%		2		μs

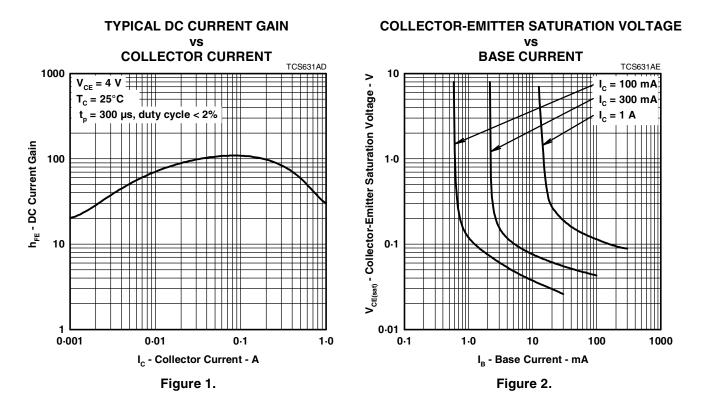
[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

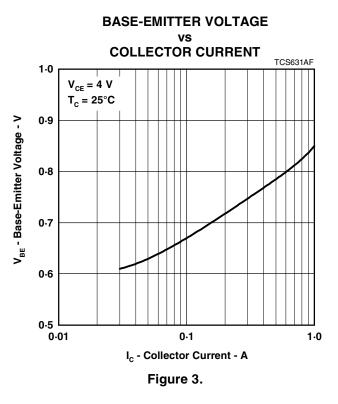


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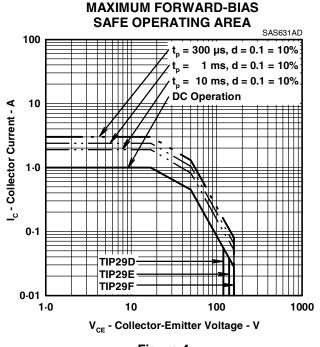
TYPICAL CHARACTERISTICS





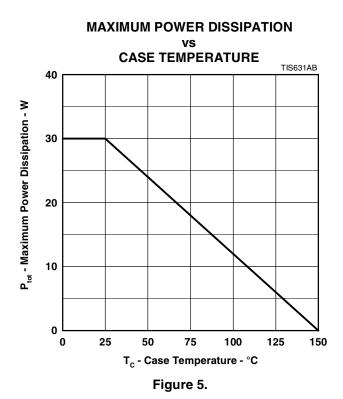
PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS









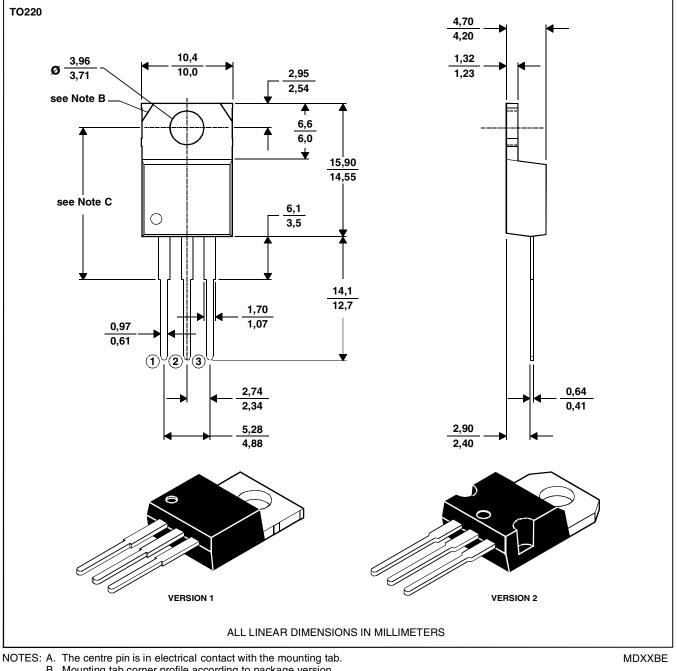
PRODUCT INFORMATION

MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



B. Mounting tab corner profile according to package version.

C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

PRODUCT INFORMATION